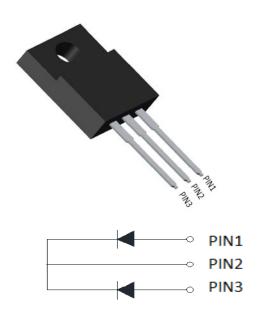




Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: ITO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRL3045FCT
Device marking code			MBRL3045FCT
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, Ta (FIG 1)	Ю	Α	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25°C	IFSM	Α	250
Current Squared Time @1ms≤t≤8.3ms Tj=25°C, rating of per diode	I2t	A2s	259
Storage Temperature	Tstg	°C	-55 ~ +150
Junction Temperature	Tj	°C	-55 ~ + 150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRL3045FCT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.55
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM Ta=25°C	0.2
	IRRM2		VRM=VRRM Ta=100°C	50

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

MBRL3045FCT

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARA	AMETER	SYMBOL	UNIT	MBRL3045FCT
Thermal Resistance	Between junction and case	R ₀ J-C	°CW	4.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRL3045FCT	Approximate 1.6	50	1000	5000	Tube

■Characteristics (Typical)

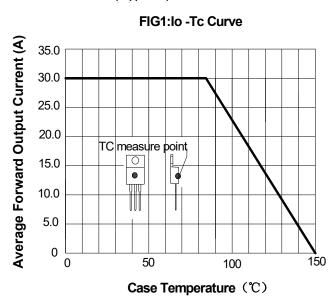


FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 1 2 5 10 20 50 100

Number of Cycles

FIG3: Forward Voltage

50

20

10

5.0

5.0

1.0

0.5

0.1

0.1

0.2

0.1

0.1

0.2

0.3

0.4

0.5

0.6

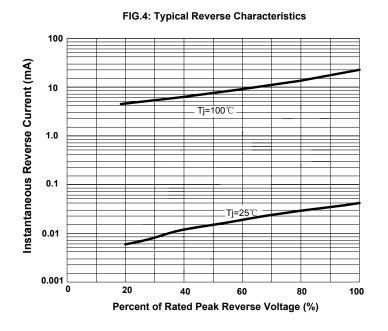
0.7

0.8

0.9

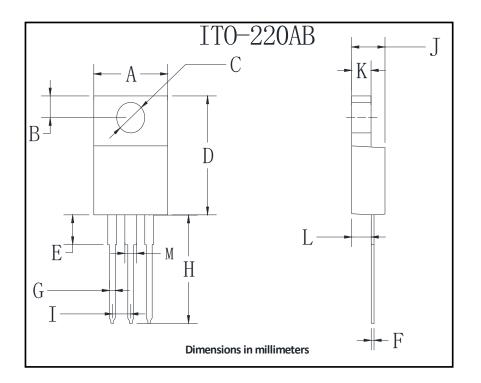
1.0

Instantaneous Forward Voltage (V)





■Outline Dimensions



ITO-220AB				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.05	3.95		
F	0.45	0.75		
G	0.45	0.75		
Н	13.4	14.2		
I	2.35	2.75		
J	4.3	4.8		
K	2.58	2.82		
L	2.58	2.82		
М	1.47	1.77		

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